

# DEPFET Status

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# Outline

- DEPFET - ILC and Belle II
- DEPFET Vertex Detectors - Design and Electronics
- Test Beam Results
- Simulation Status

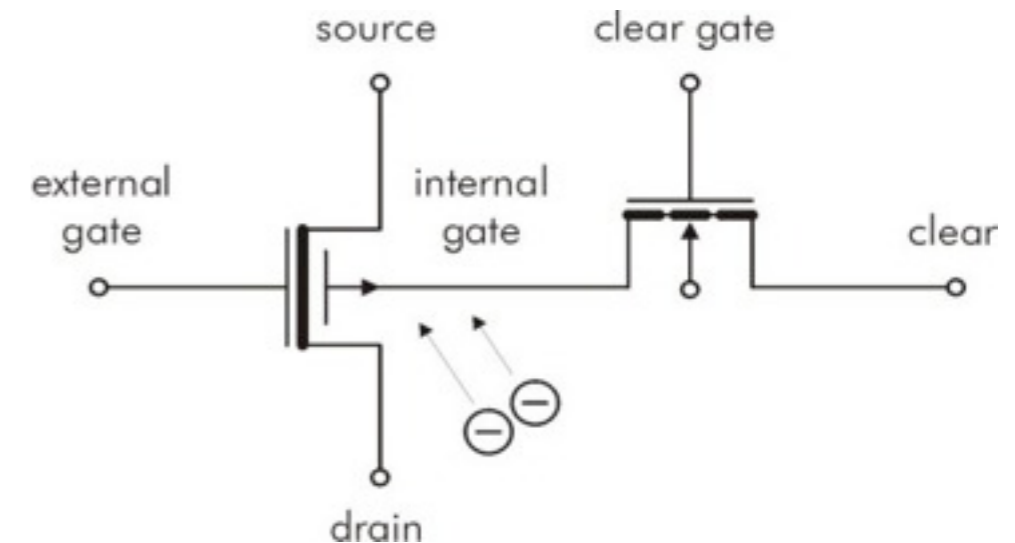
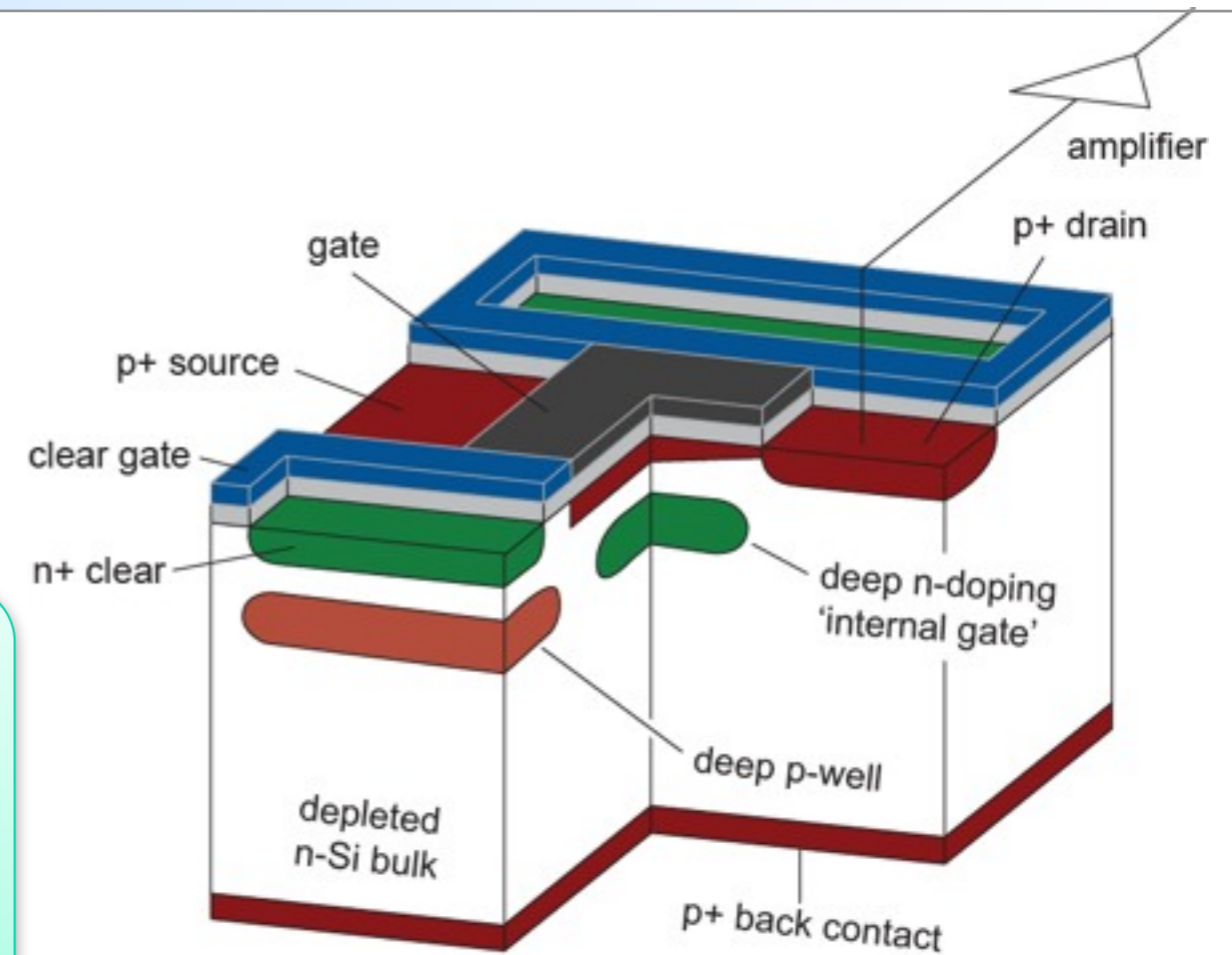
# Reminder - DEPFET Technology

- Each pixel is a p-channel FET on a completely depleted bulk (sideward depletion). Charge is collected by drift
- A deep n-implant creates a potential minimum for electrons under the gate (internal gate)

- Signal electrons accumulate in the internal gate and modulate the transistor current ( $g_q \approx 400 \text{ pA/e}^-$ )
- Rolling shutter row-wise readout
- Accumulated charge can be removed by a clear contact

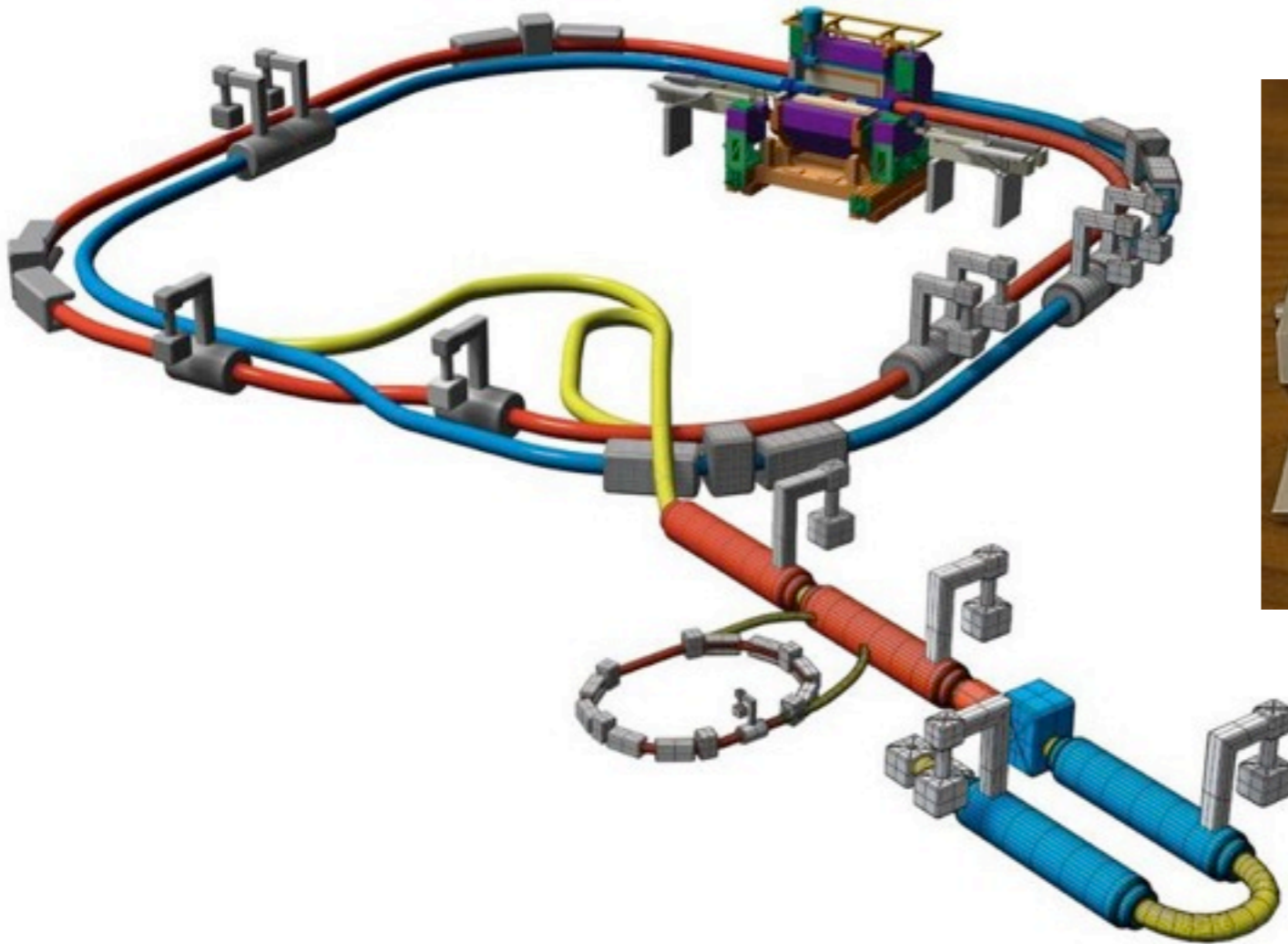
- Detection, fast charge collection and internal amplification
- Excellent signal-to-noise ratio
- Low power consumption
- Thin detectors

**Features**



# Belle II PXD: A Boost in Development

- DEPFET pixel sensors used for the vertex detector of Belle II (2 pixel layers)
  - To be operated at SuperKEK B, Y(4s) resonance, luminosity  $8 \times 10^{35} \text{ cm}^{-2}\text{s}^{-1}$



- Installation foreseen for 2015: Accelerated development

# DEPFET Design - ILC vs Belle II

- Experimental conditions - ILC vs Belle II

	ILC	Belle II
Occupancy	0.13 hits/ $\mu\text{m}^2/\text{s}$	0.1 hits/ $\mu\text{m}^2/\text{s}$
Radiation	< 100 krad/year	< 2 Mrad/year
Duty cycle	1/200	1
Frame time	25-100 $\mu\text{s}$	20 $\mu\text{s}$
Momentum range	All momenta	Low momentum (< 1 GeV)
Acceptance	6°-174°	17°-155°

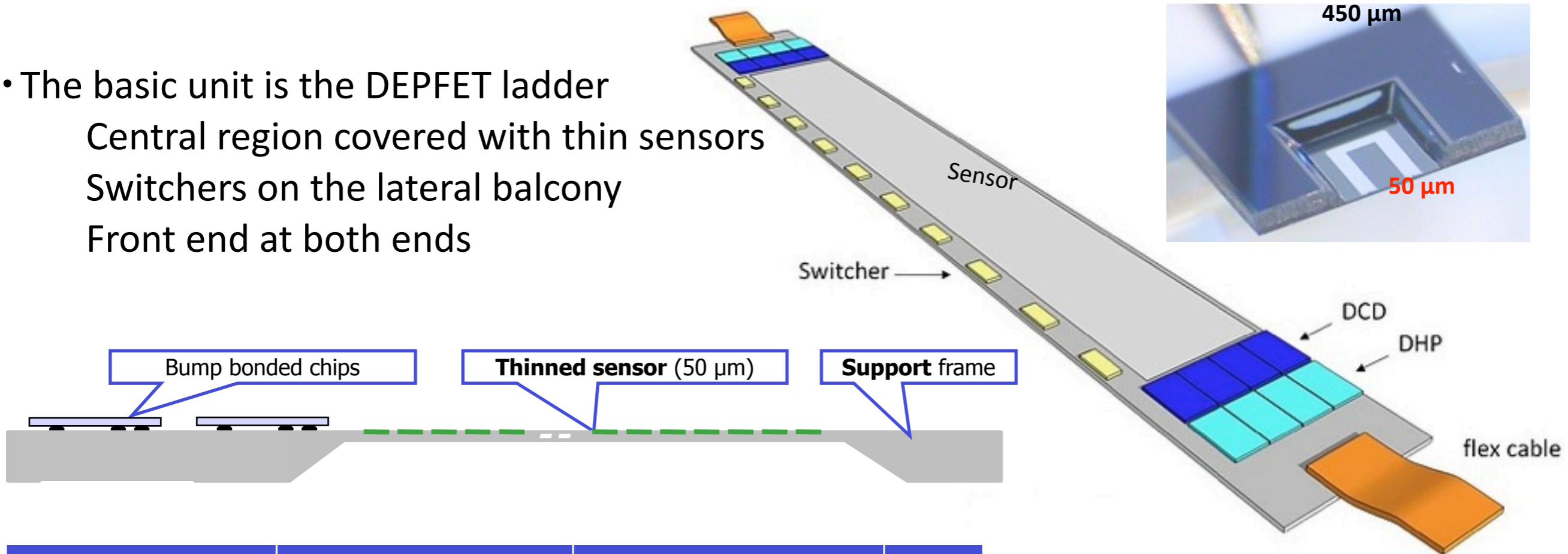
In several aspect Belle II more challenging than ILC

at ILC: focus on best possible spatial resolution - small pixels, thinnest possible layers

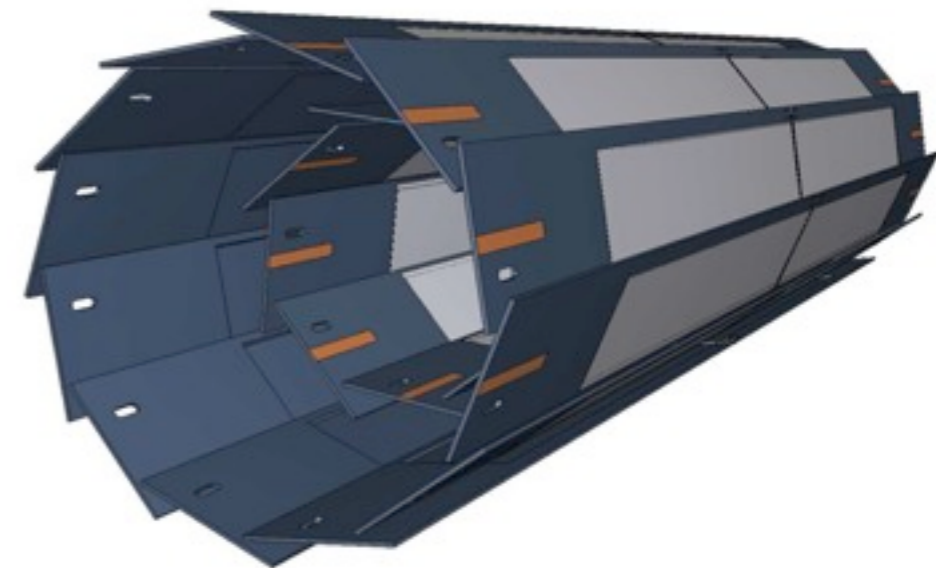
at Belle II: Less stringent requirements (limits from multiple scattering at low momentum), number of pixels constrained due to continuous readout

# DEPFET Vertex Detectors

- The basic unit is the DEPFET ladder
  - Central region covered with thin sensors
  - Switchers on the lateral balcony
  - Front end at both ends



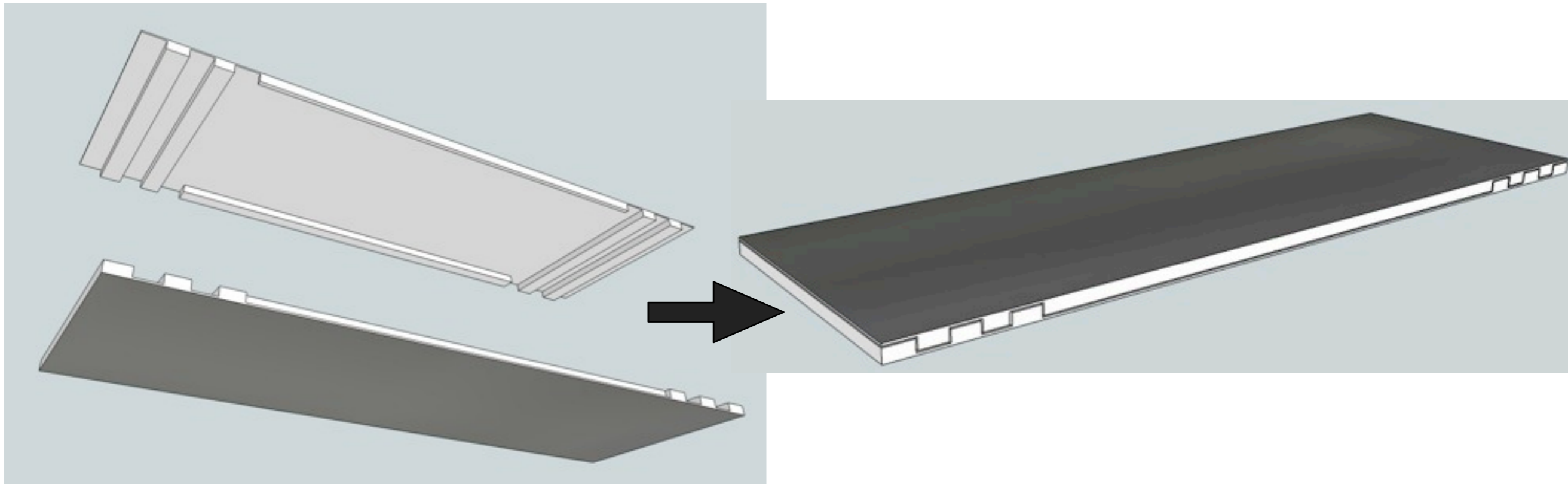
	Old ILD 5-layer layout	Belle II	
Radii	15.5, 26, 38, 49, 60	14, 22	mm
Ladder length	100 (L0), 250 (L1-L4)	136 (L0), 169 (L1)	mm
Sensitive width	13 (L0), 22 (L1-L4)	12.5 (L0-L1)	mm
Number of ladders	8, 8, 12, 16, 20	8, 12	
Pixel size	25x25 (L0-L4)	50x50 (L0), 50x75 (L1)	$\mu\text{m}^2$
Row rate	40	10	MHz
Number of pixels	800	8	Mpix



# DEPFETs: Mechanical concepts

- DEPFET technology compatible with 5 individual layers (original concept) or 3 double layers

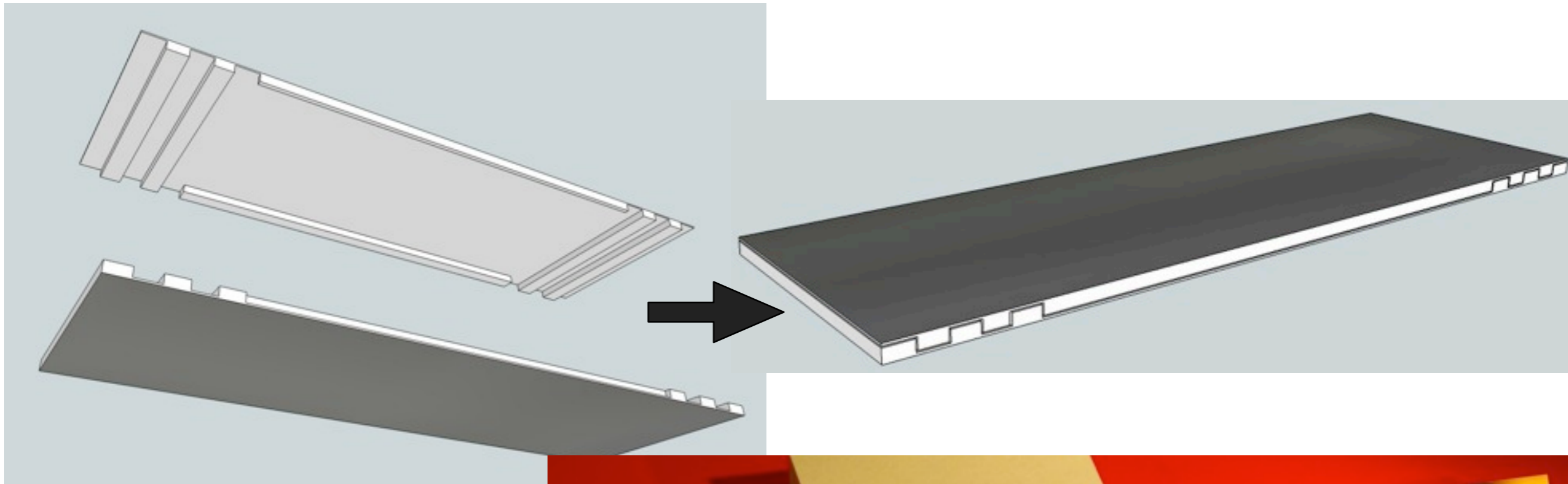
First ideas for silicon-only double layers:



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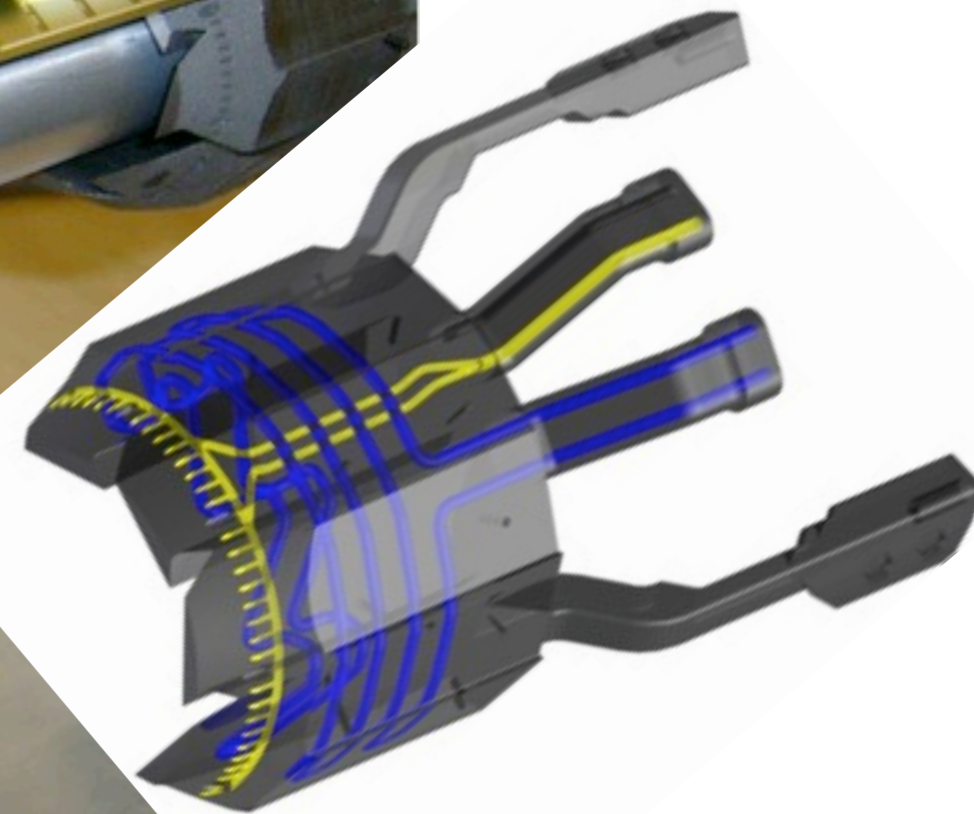
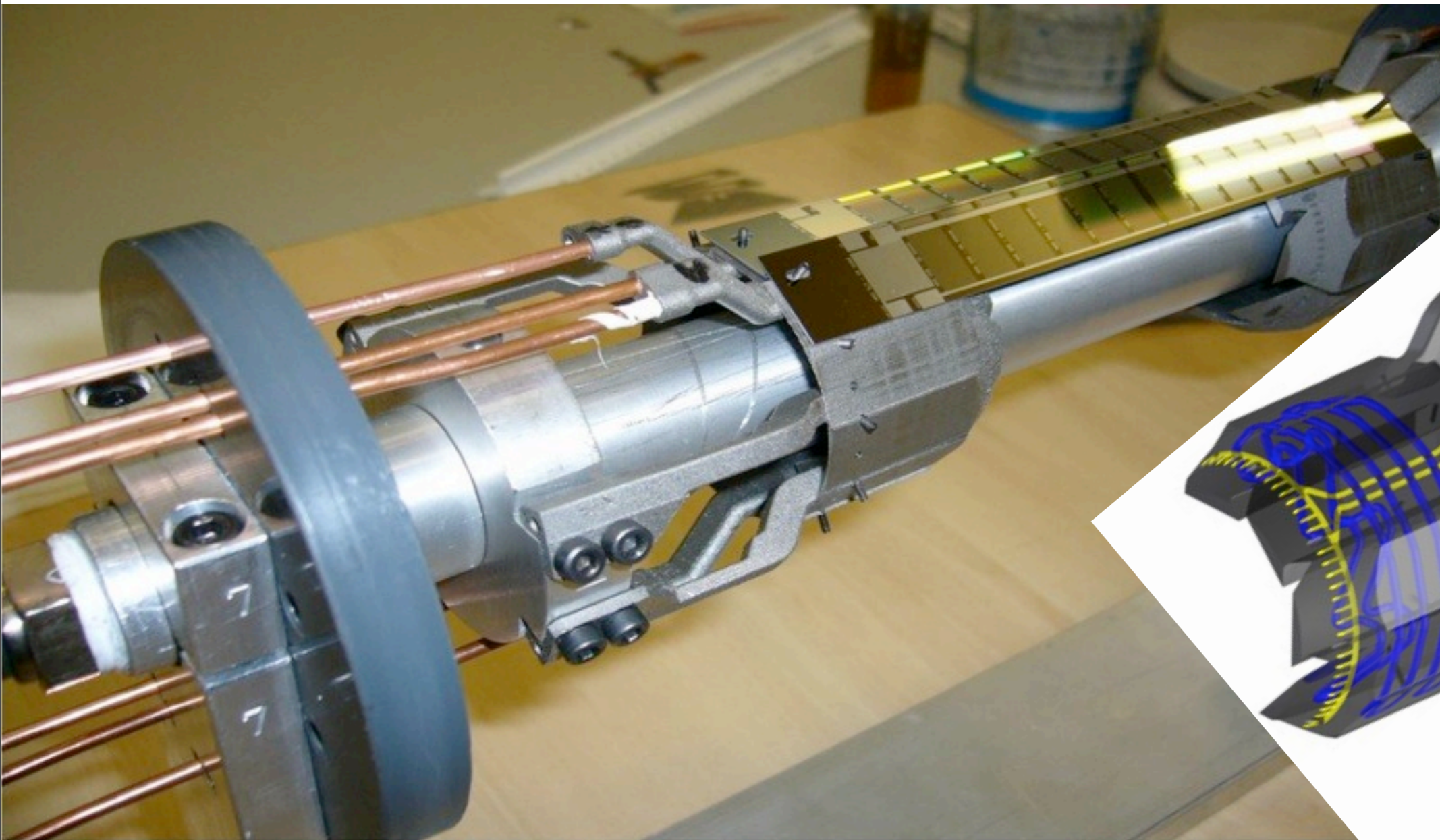
Fully tested low-mass ceramic micro-joint connections of silicon modules





# DEPFETs: Mechanical Concepts

- Fully developed mechanical design for Belle-II
  - includes CO<sub>2</sub> cooling of support structure and air cooling of sensors



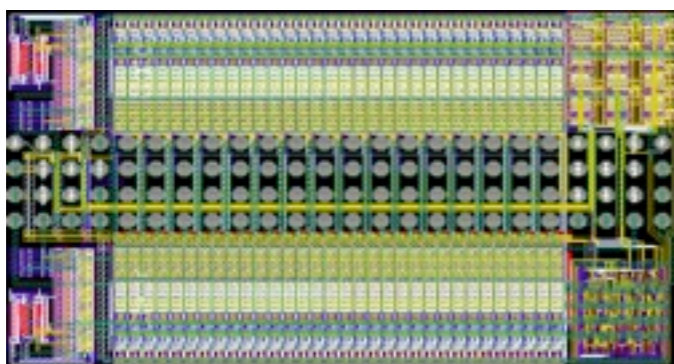
blue: CO<sub>2</sub>  
yellow: Air

# On Detector Electronics - Status

The full-size close to final versions of the ASICs are designed, produced and found to work

## SwitcherB

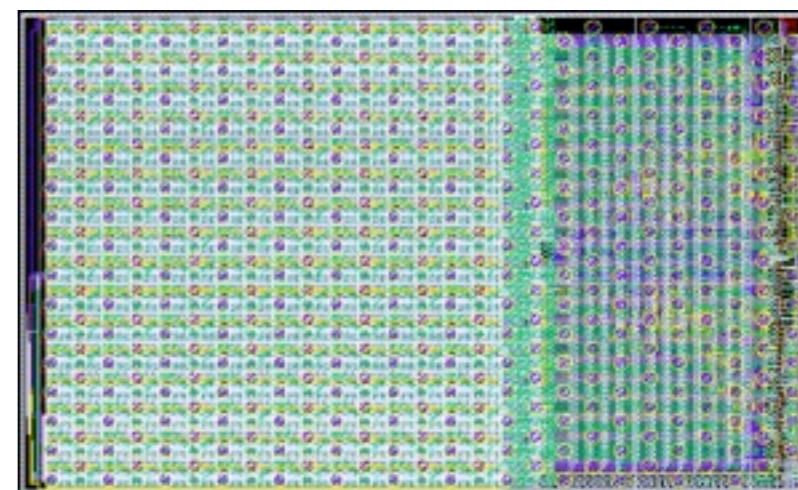
Row control



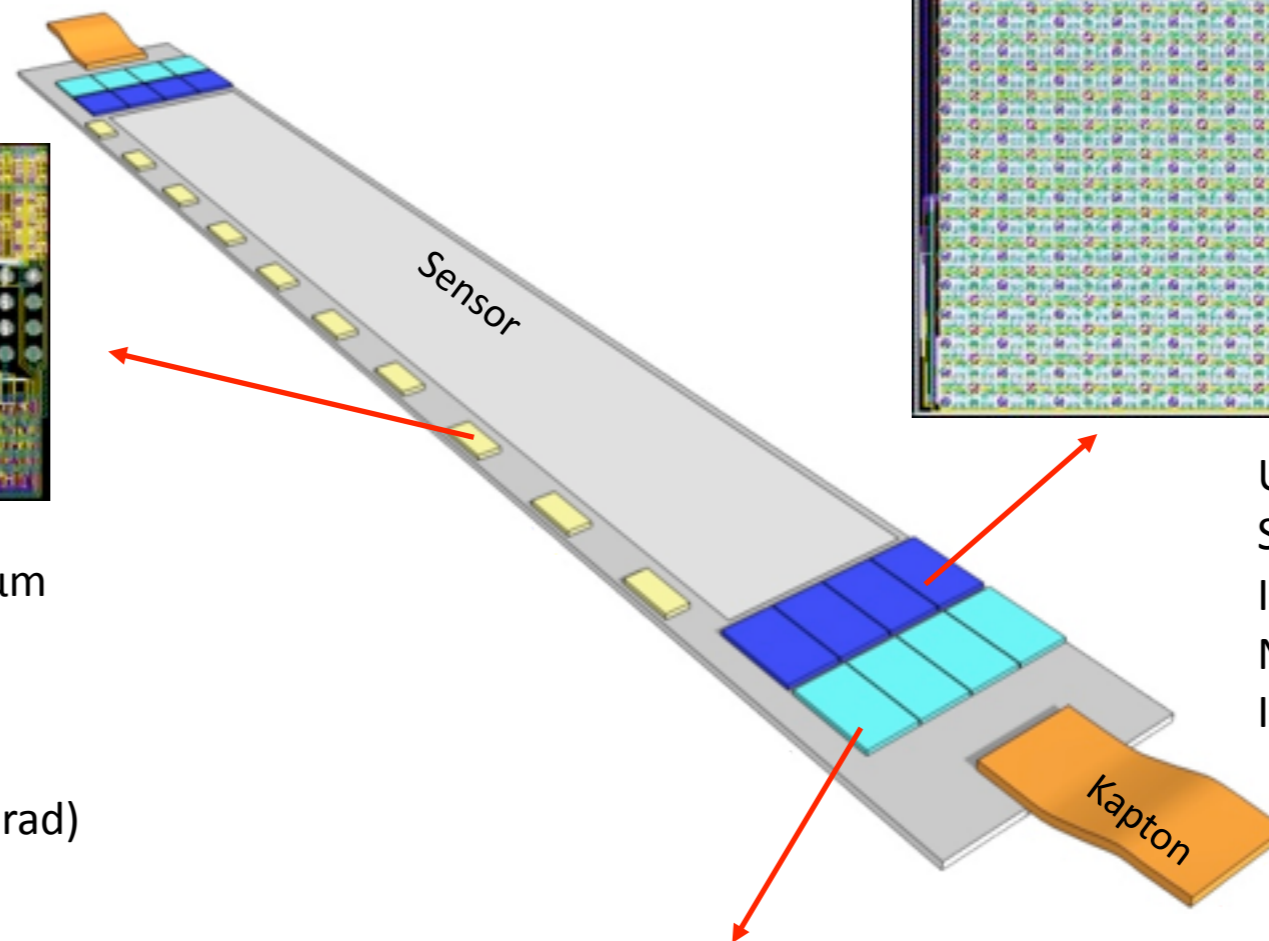
AMS high voltage 0.35  $\mu\text{m}$   
Size  $3.6 \times 2.1 \text{ mm}^2$   
Gate and Clear signal  
Fast HV up to 30V  
Rad. Hard proved (36 Mrad)

## DCDB (Drain Current Digitizer)

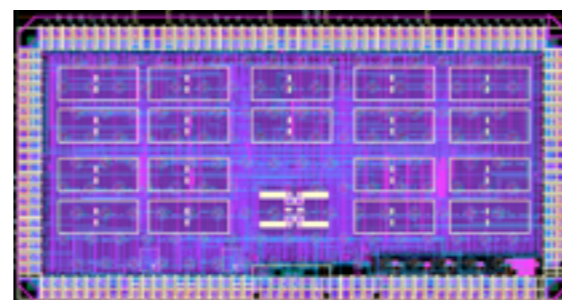
Analog frontend



UMC 180 nm  
Size  $3.3 \times 5.0 \text{ mm}^2$   
Integrated ADC  
Noise 40 nA  
Irradiation up to 7Mrad



## DHP (Data Handling Processor)

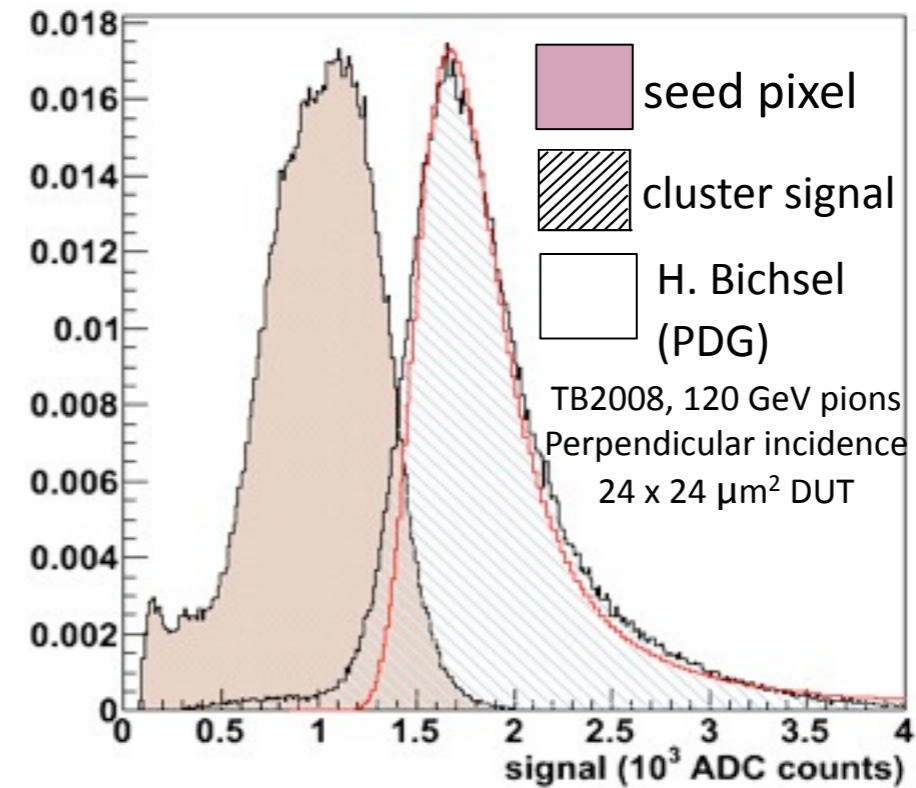
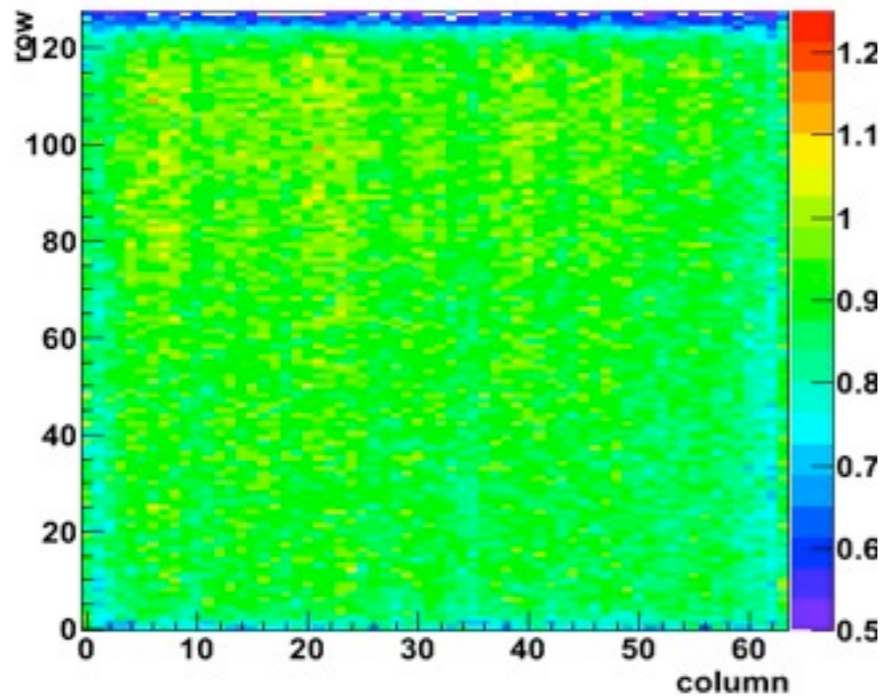


IBM CMOS 90 nm (TSMC 65 nm)  
Stores raw data and pedestals  
Common mode and pedestal correction  
Data reduction (zero suppression)  
Timing signal generation

The layout of the module periphery is ready as well

# Testbeam Results - ILC Prototypes

Gain map: Deviation from average seed signal



- 64x128, 24x24x450  $\mu\text{m}^3$  CCG, 6  $\mu\text{m}$  (TB2008)

$$g_q = 363 \text{ pA/e}^-$$

- 64x256, 20x20x450  $\mu\text{m}^3$  CCG, 5  $\mu\text{m}$  (TB2009)

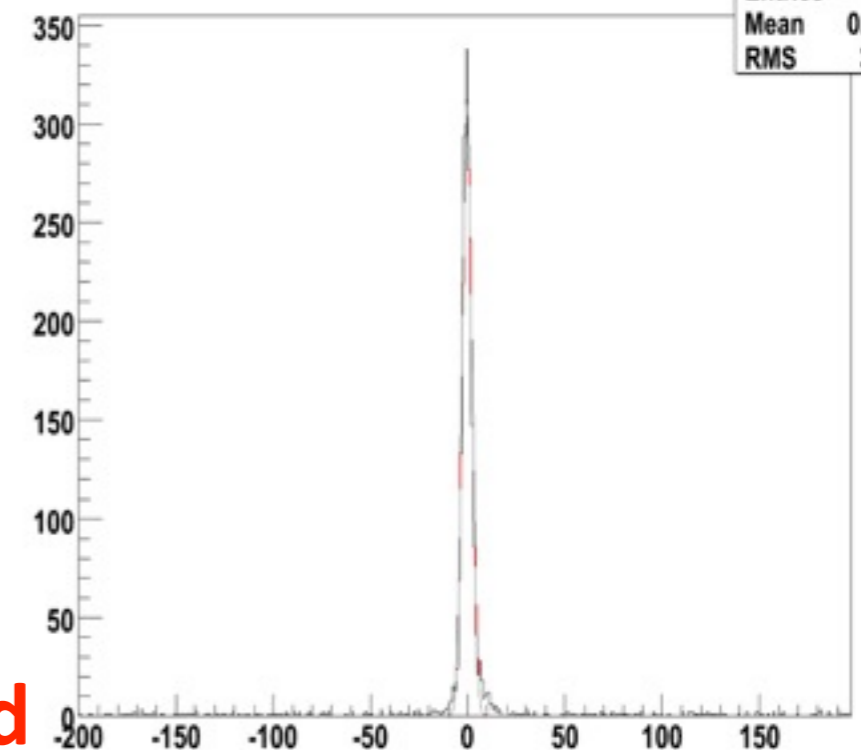
$$g_q \sim 650 \text{ pA/e}^-$$

- Resolution  $\sigma \sim 1 \mu\text{m}$ , 20x20x450  $\mu\text{m}^3$ , analog readout with charge interpolation

**ILC Design**

**→ Extensively tested**

YResidual\_d3



# Testbeam Results: Belle II Thinned Prototypes

## Belle II design

Sensor 32x64 pixels

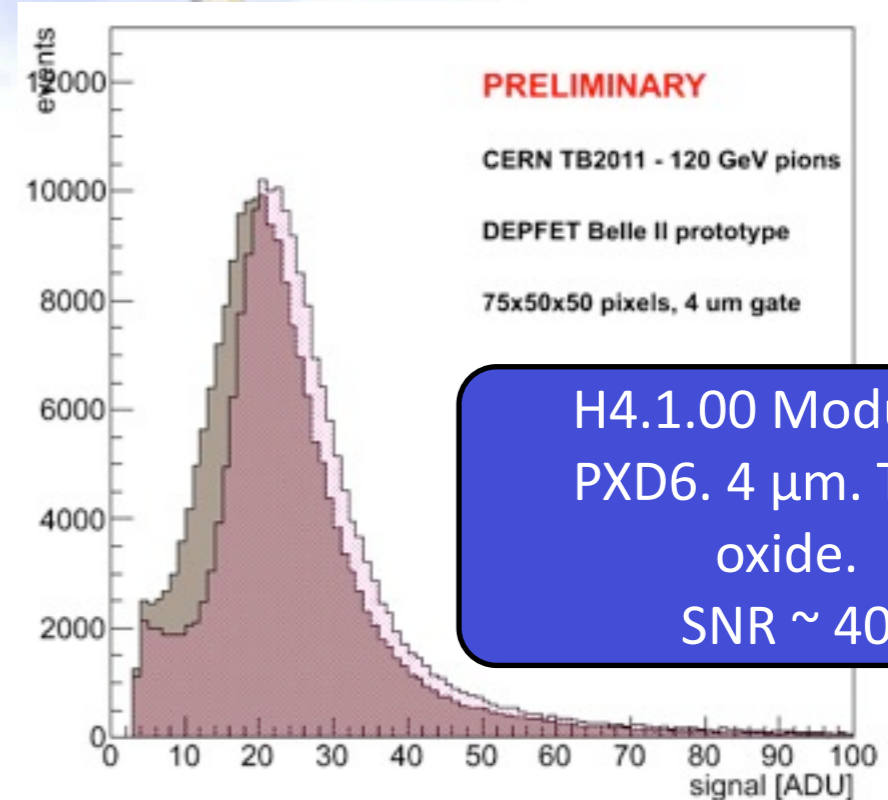
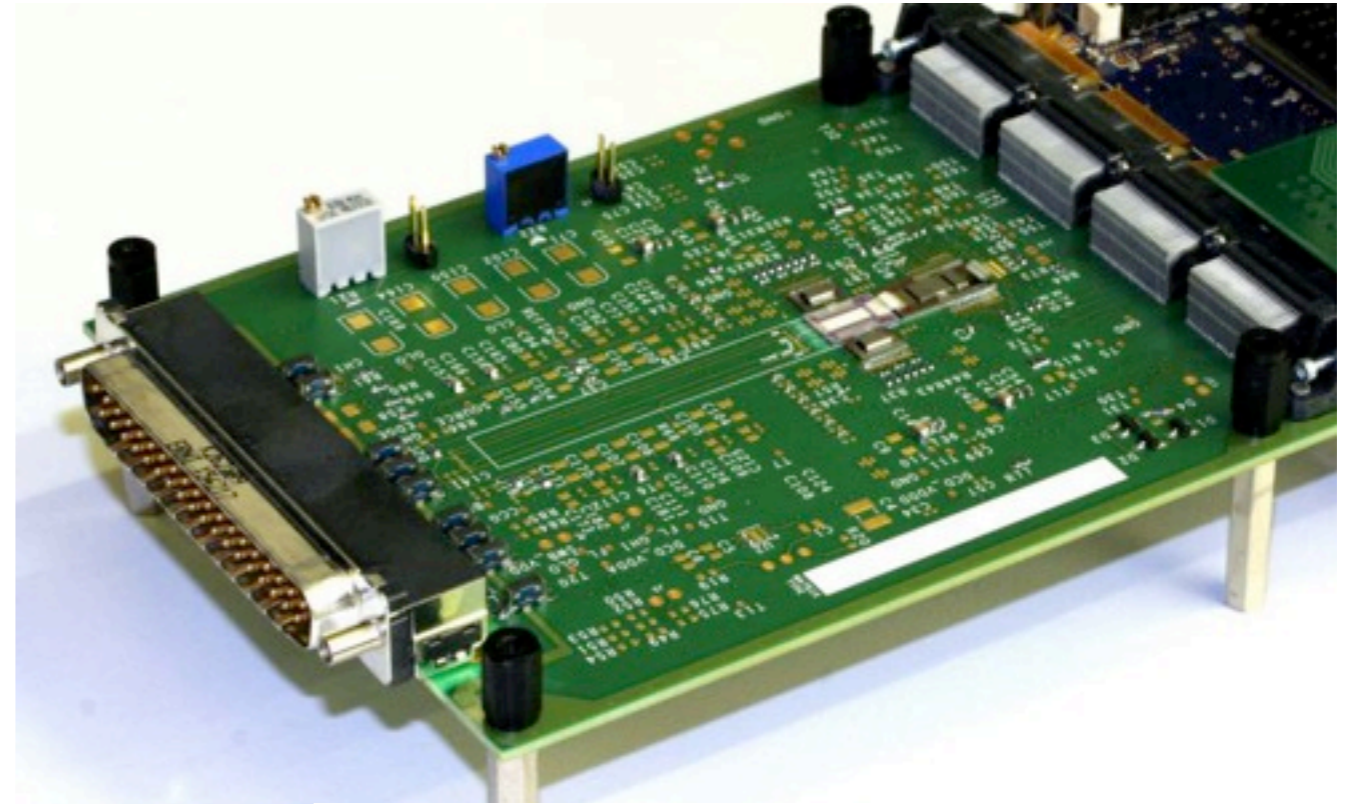
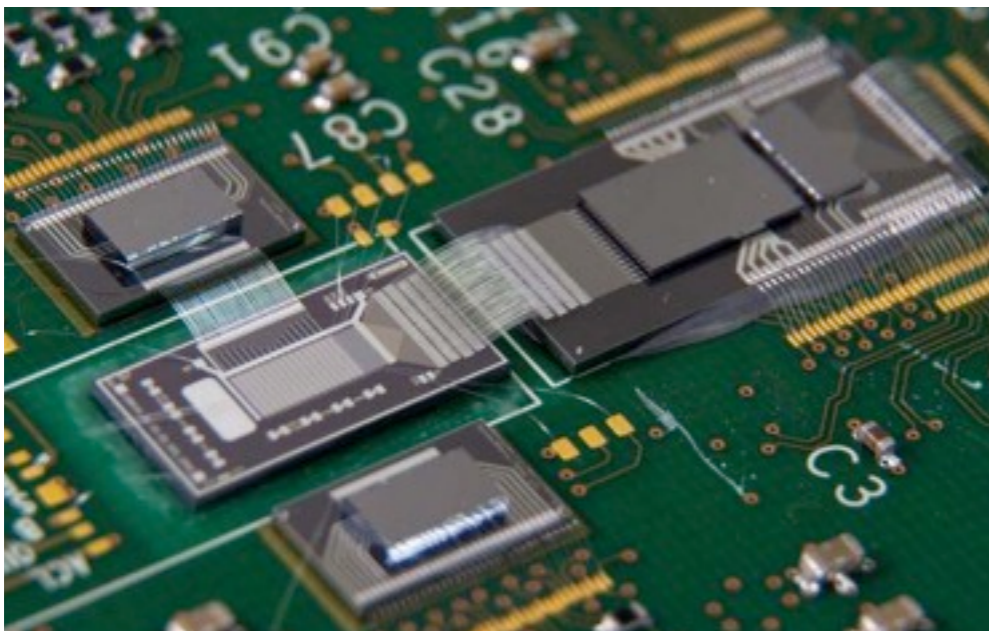
50x75x50  $\mu\text{m}^3$

SwitcherB and DCDB at full speed

DCDB readout at 320MHz

100 ns row time

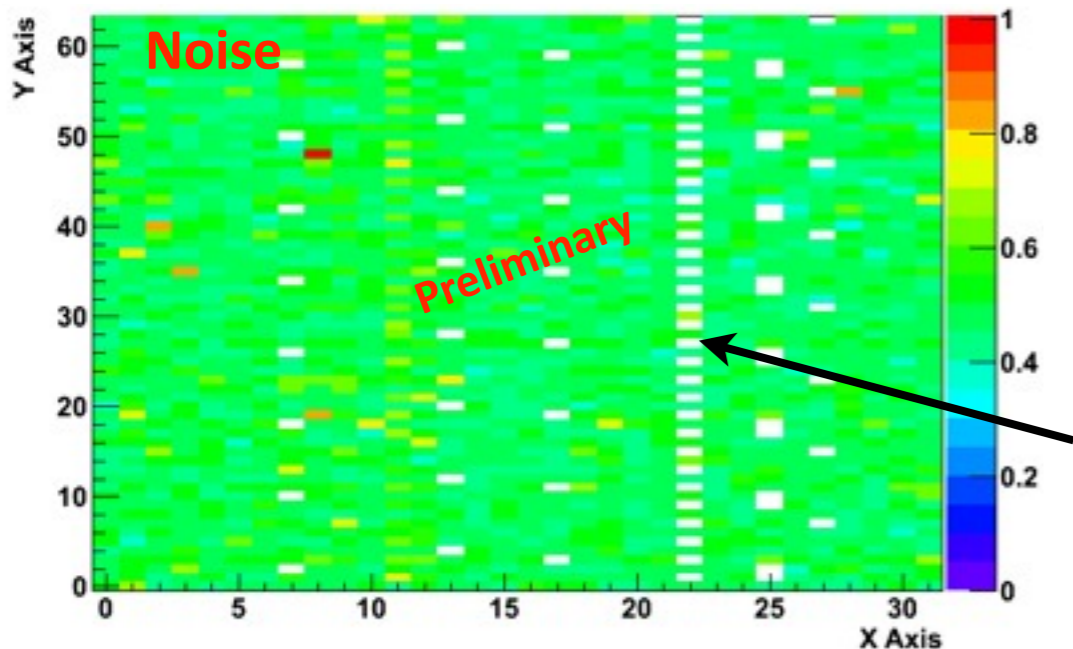
**Close to final  
specs!**



Based on the valuable information obtained with the PXD6, the final Belle II production (PXD9) is already launched

# Testbeam Results: Belle II Thinned Prototypes

- Homogeneous behavior observed in noise and gain

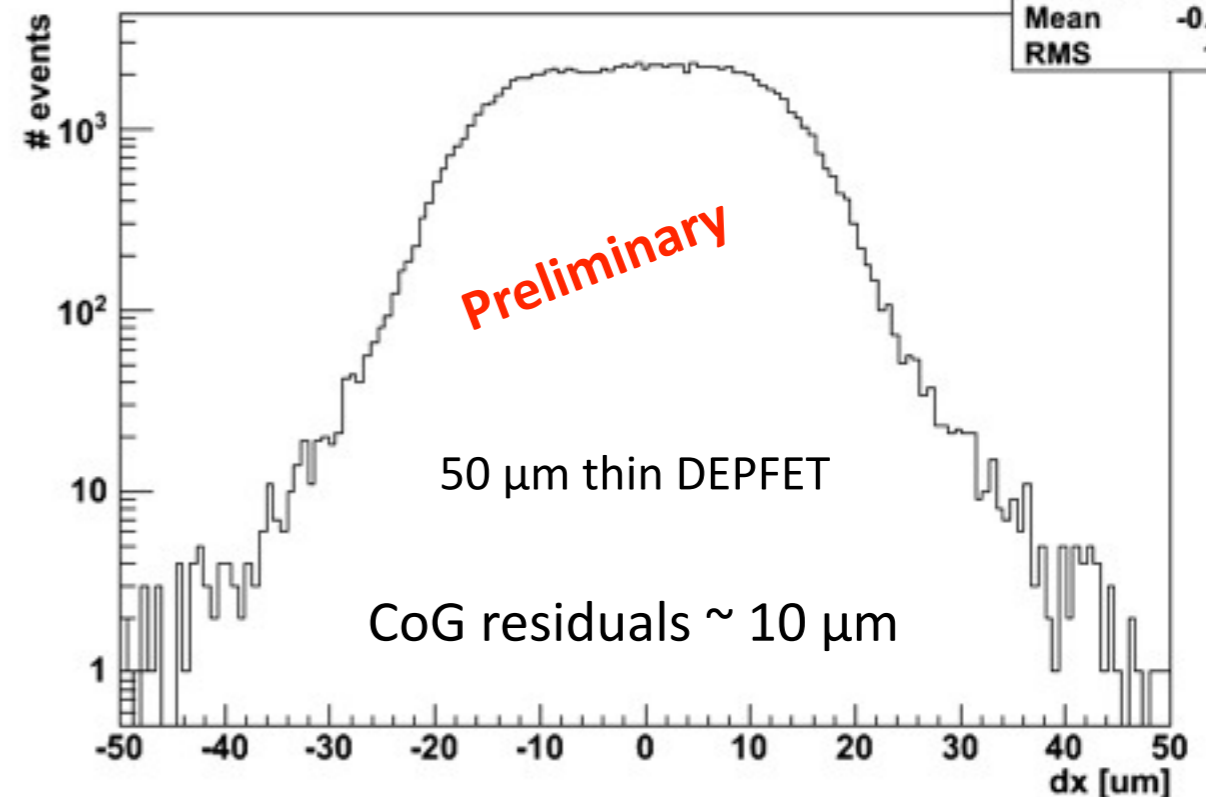


some dead channels  
due to a few non-  
working ADC  
channels

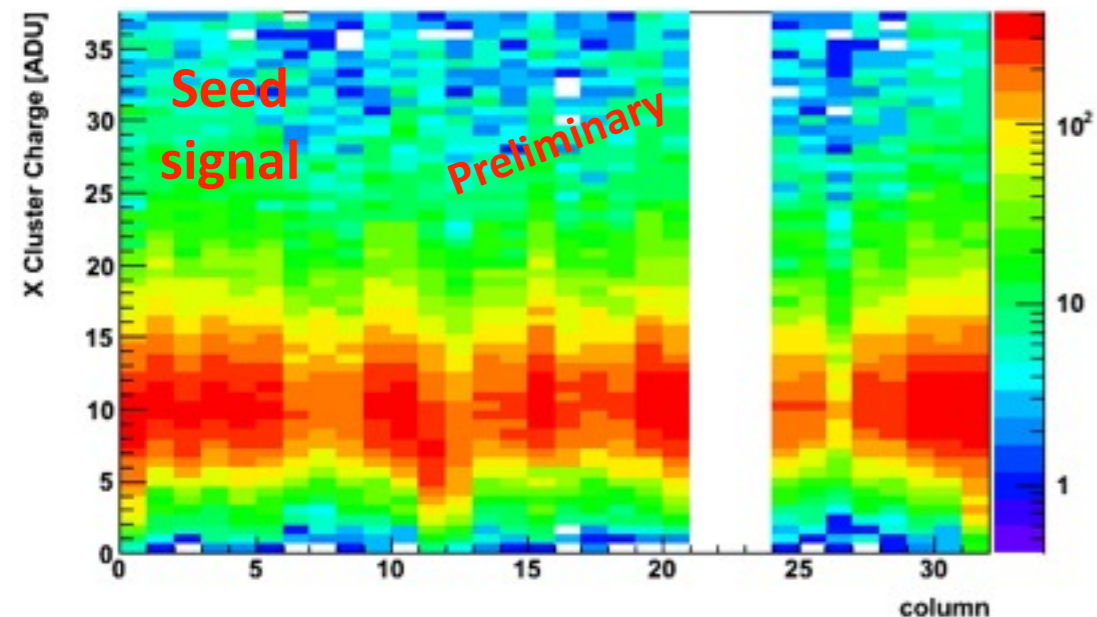
spatial resolution  $\sim 10 \mu\text{m}$

Homogeneous noise map (0.5 LSB at 100 MHz)

Hit Residuals X

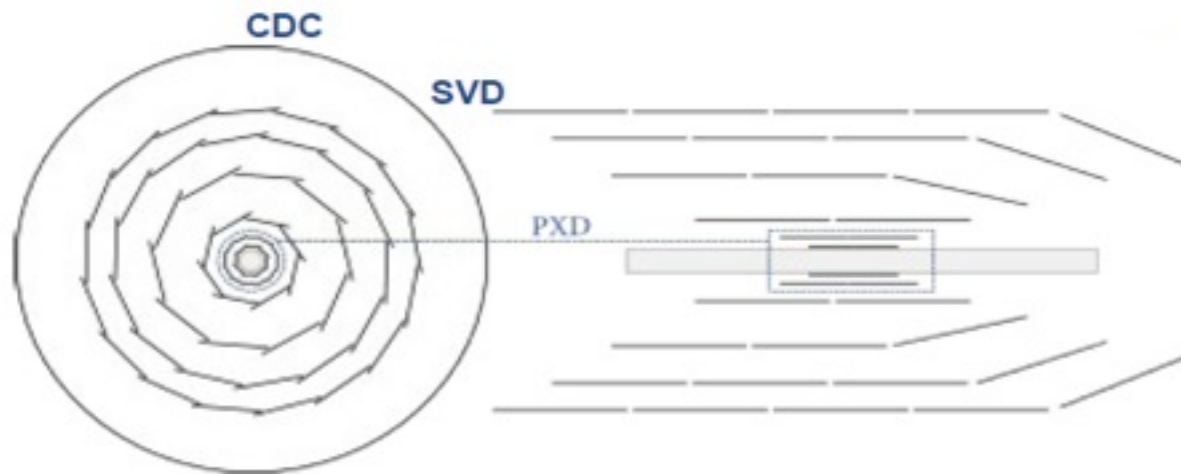
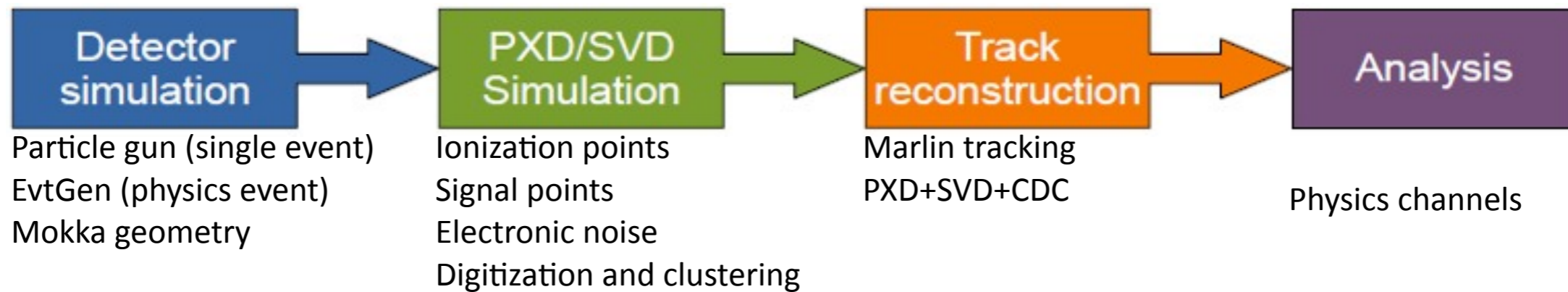


CoG residuals  $\sim 10 \mu\text{m}$



Column wise variations in the order 10%

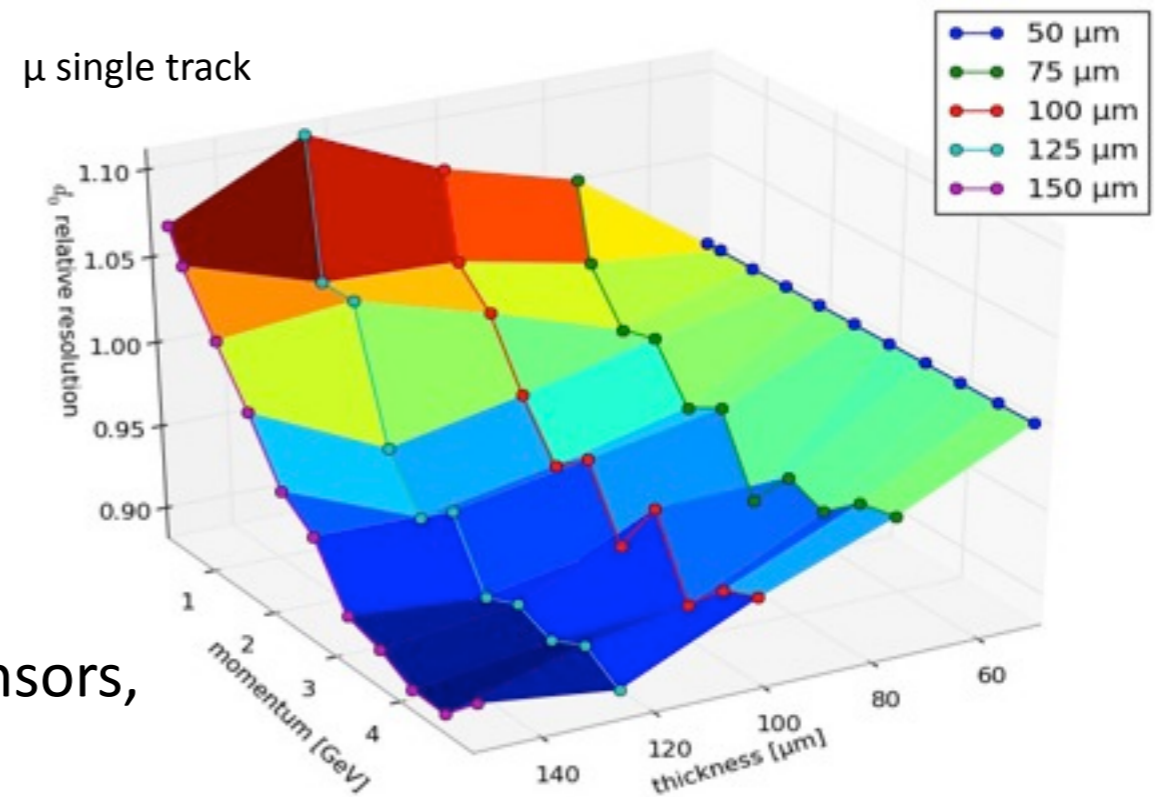
# A Full Simulation Chain



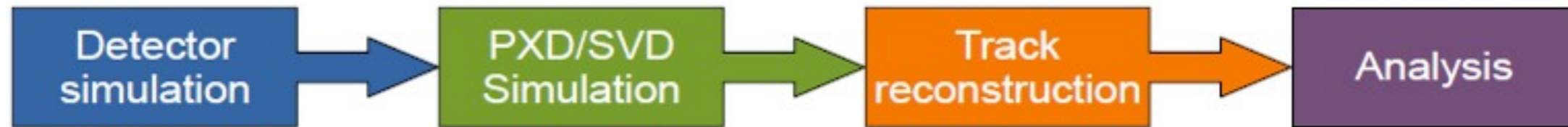
- Digitizer (Geant4) tuned with TBeam data:
  - Electric noise
  - Electric field in Si (charge collection time)
  - Lorentz angle in magnetic fields

- Optimization studies:
- Sensor thickness
  - Pixel size
  - Inner layer radius

Best performance for Belle-II with 75  $\mu\text{m}$  thick sensors, up from originally studied 50  $\mu\text{m}$



# A Full Simulation Chain



Particle gun (single event)  
EvtGen (physics event)  
Mokka geometry

Ionization points  
Signal points  
Electronic noise  
Digitization and clustering

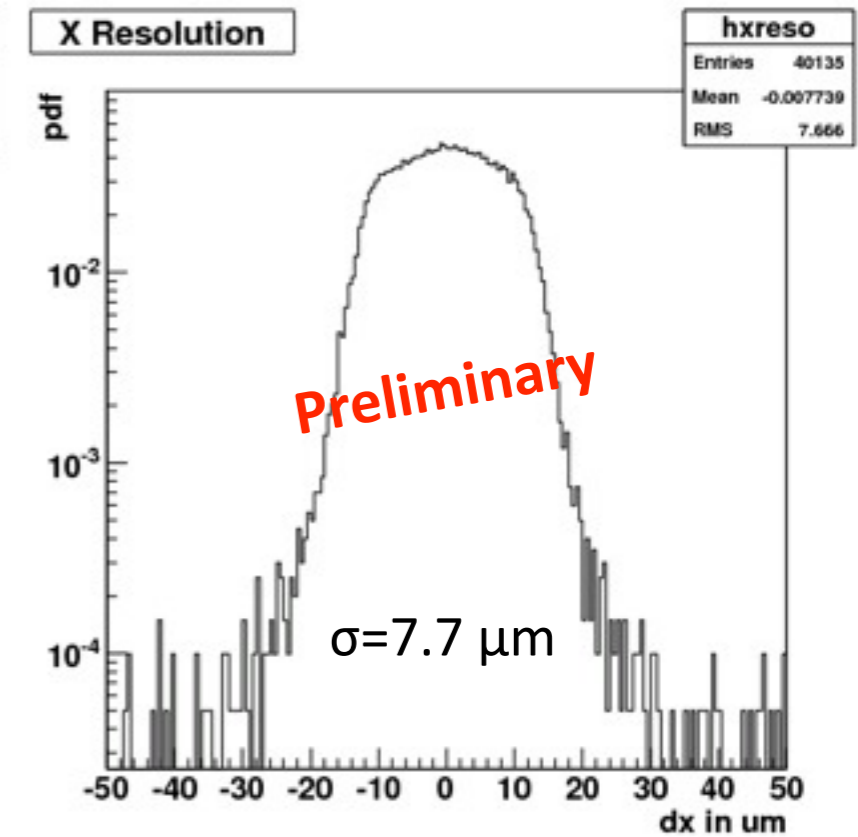
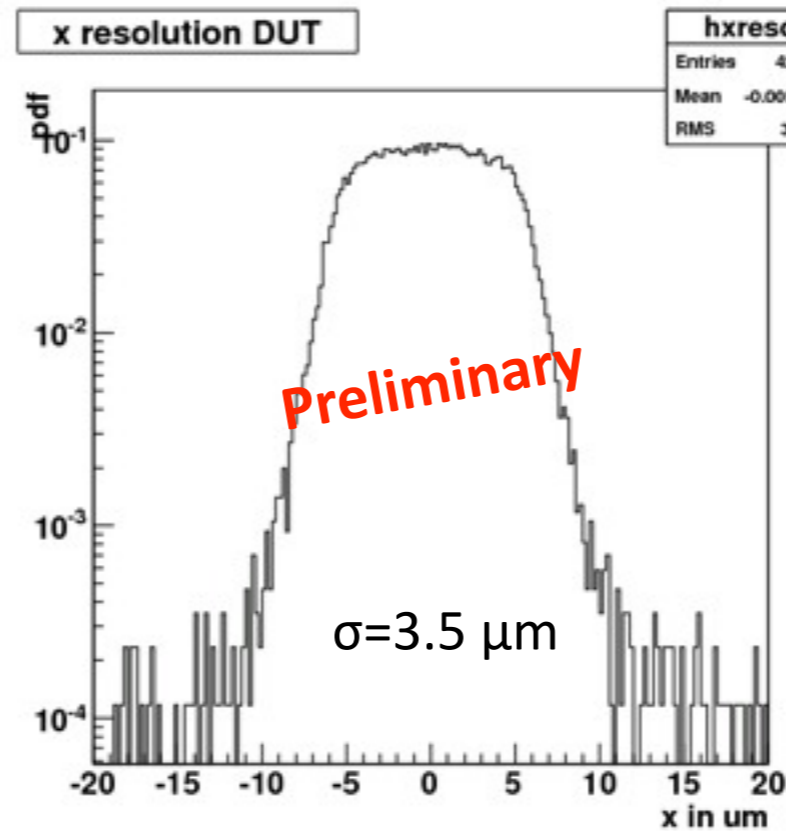
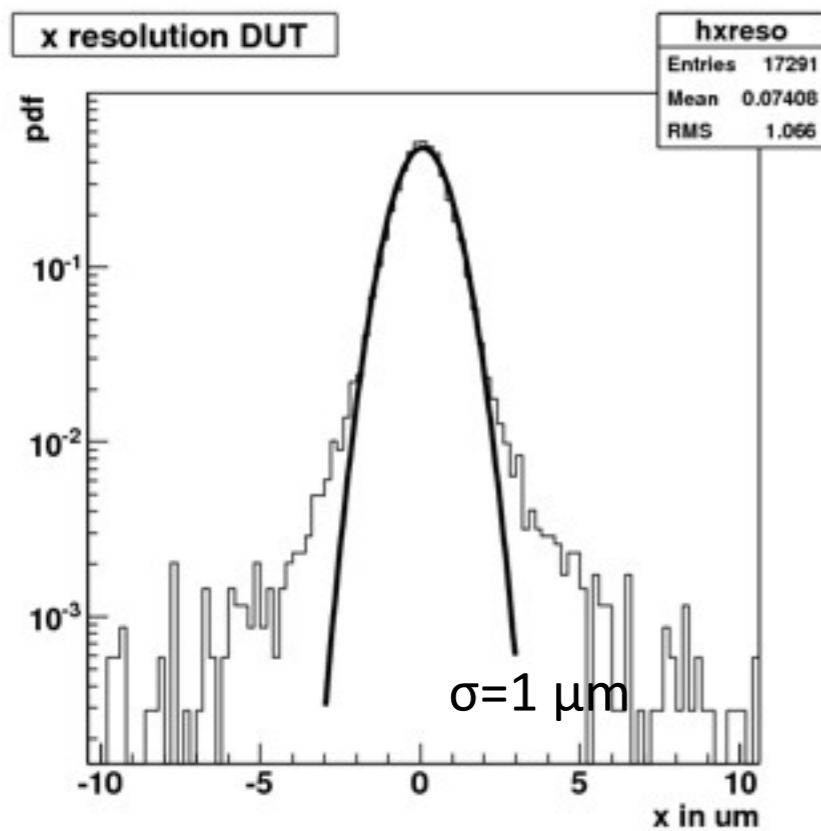
Marlin tracking  
PXD+SVD+CDC

Physics channels

**Test Beam Data**  
20x20x450  $\mu\text{m}^3$   
Single point resolution: 1  $\mu\text{m}$

**ILC (Simulation)**  
20x20x50  $\mu\text{m}^3$   
Single point resolution: 3.5  $\mu\text{m}$

**Belle II (Simulation)**  
50x50x75  $\mu\text{m}^3$   
Single point resolution: 7.7  $\mu\text{m}$



→ Compare to  $\sim 10 \mu\text{m}$  seen in TB, with thinner sensors and wider pixel pitch in one dimension

# Summary

- DEPFET by now is a mature technology for high-resolution, low mass pixel detectors
- Accelerated development for the Belle II pixel detector
- Full electronic chain established, ASICS designed
- Mechanical concepts established: All silicon solution with micro-joints used for Belle II PXD, CO<sub>2</sub> and air cooling
- Thin sensors successfully operated in test beams: signal/noise ~ 40 achieved
- ▶ Design for ILD profits substantially from Belle II experience